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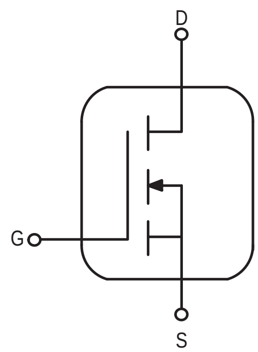
MRF1508 (Cancelled)

MRF1508T1

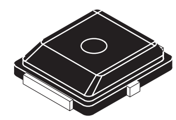
The RF MOSFET Line
RF Power Field Effect Transistor
N–Channel Enhancement–Mode Lateral MOSFETs

The MRF1508 is designed for broadband commercial and industrial applications at frequencies to 520 MHz. The high gain and broadband performance of this device makes it ideal for large–signal, common source amplifier applications in 12.5 volt mobile FM equipment.

- Specified Performance @ 520 MHz, 12.5 Volts
  Output Power — 8 Watts
  Power Gain — 14 dB
  Efficiency — 60%
- Characterized with Series Equivalent Large–Signal Impedance Parameters
- Excellent Thermal Stability
- Capable of Handling 20:1 VSWR, @ 15.5 Vdc, 520 MHz, 2 dB Overdrive
- RF Power Plastic Surface Mount Package
- Broadband UHF/VHF Demonstration Amplifier Information Available Upon Request
- Available in Tape and Reel by Adding T1 Suffix to Part Number. T1 Suffix = 1,000 Units per 12 mm, 7 Inch Reel.



**8 W, 520 MHz, 12.5 V
LATERAL N–CHANNEL
BROADBAND
RF POWER MOSFET**



**CASE 466–02, STYLE 1
(PLD 1.5)**

PLASTIC

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DSS}	40	Vdc
Gate–Source Voltage	V_{GS}	±20	Vdc
Drain Current — Continuous	I_D	4	Adc
Total Device Dissipation @ T_C = 25°C (1) Derate above 25°C	P_D	62.5 0.50	Watts W/°C
Storage Temperature Range	T_{stg}	–65 to +150	°C
Operating Junction Temperature	T_J	150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2	°C/W

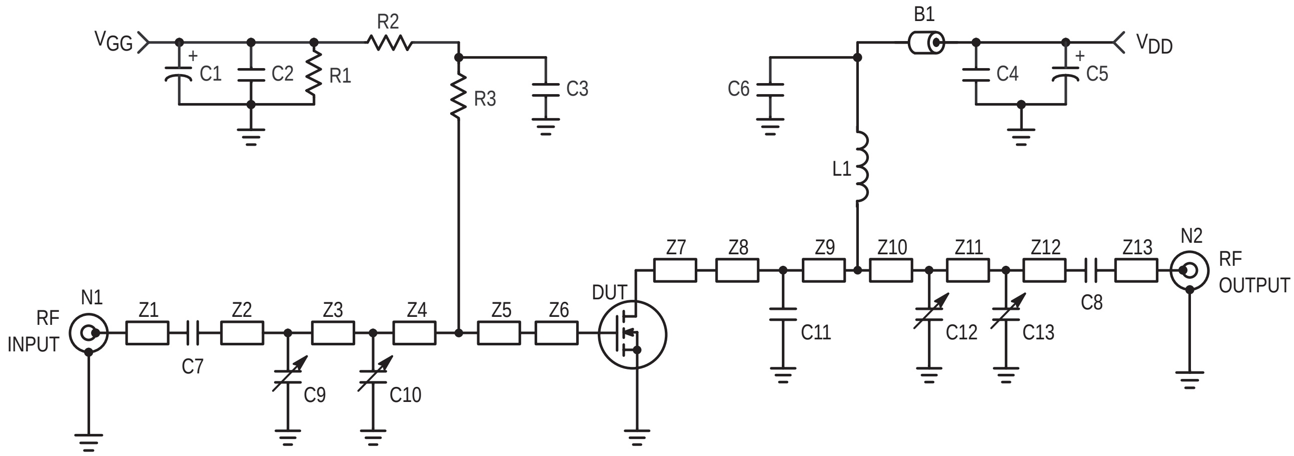
(1) Calculated based on the formula $P_D = \frac{T_J - T_C}{R_{\theta JC}}$

NOTE – **CAUTION** – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

REV 1

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Zero Gate Voltage Drain Current (V_{DS} = 40 Vdc, V_{GS} = 0)	I_{DSS}	—	—	10	μAdc
Gate–Source Leakage Current (V_{GS} = 20 Vdc, V_{DS} = 0)	I_{GSS}	—	—	1	μAdc
ON CHARACTERISTICS					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 100 μA)	$V_{GS(th)}$	2.4	3	—	Vdc
Drain–Source On–Voltage (V_{GS} = 10 Vdc, I_D = 2 Adc)	$V_{DS(on)}$	0.3	0.5	—	Vdc
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 2 Adc)	g_{fs}	1.3	1.75	—	S
DYNAMIC CHARACTERISTICS					
Input Capacitance (V_{DS} = 12.5 Vdc, V_{GS} = 0, f = 1 MHz)	C_{iss}	—	47	—	pF
Output Capacitance (V_{DS} = 12.5 Vdc, V_{GS} = 0, f = 1 MHz)	C_{oss}	—	35	—	pF
Reverse Transfer Capacitance (V_{DS} = 12.5 Vdc, V_{GS} = 0, f = 1 MHz)	C_{rss}	—	4.1	—	pF
FUNCTIONAL TESTS (In Motorola Test Fixture)					
Common–Source Amplifier Power Gain (V_{DD} = 12.5 Vdc, P_{out} = 8 Watts, I_{DQ} = 150 mA, f = 520 MHz)	G_{ps}	12	14	—	dB
Drain Efficiency (V_{DD} = 12.5 Vdc, P_{out} = 8 Watts, I_{DQ} = 150 mA, f = 520 MHz)	η	55	60	—	%



B1	Fair Rite Products Long Ferrite Bead
C1, C5	10 µF, 50 V Electrolytic Capacitor
C2, C4	0.1 µF, 100 mil Chip Capacitor
C3, C6, C7, C8	130 pF, 100 mil Chip Capacitor
C9	0.8–8 pF, Variable Capacitor, Gigatrim
C10	0.8–18 pF, Variable Capacitor, Johanson
C11	16 pF, 100 mil Chip Capacitor
C12	0.8–18 pF, Variable Capacitor, Johanson
C13	0.8–8 pF, Variable Capacitor, Gigatrim
L1	4 Turns, #20 AWG Enamel Coil, 0.1″ ID
N1, N2	Type–N Flange Mount Connector
R1	1.1 MΩ, 1/4 W Carbon Resistor
R2	1.0 kΩ, 0.1 W Chip Resistor
R3	1 kΩ, 1/4 W Carbon Resistor

Z1, Z13	0.290″ x 0.081″ Microstrip
Z2	0.070″ x 0.217″ Microstrip
Z3	2.950″ x 0.217″ Microstrip
Z4	0.150″ x 0.217″ Microstrip
Z5	0.250″ x 0.217″ Microstrip
Z6	0.250″ x 0.0073″ Microstrip AIO2
Z7	0.250″ x 0.0073″ Microstrip AIO2
Z8	0.050″ x 0.217″ Microstrip
Z9	0.100″ x 0.217″ Microstrip
Z10	0.150″ x 0.217″ Microstrip
Z11	1.500″ x 0.217″ Microstrip
Z12	1.550″ x 0.217″ Microstrip
Board	Glass Teflon®, 31 mils, 2 oz. Copper

Figure 1. 500 – 520 MHz Broadband Test Circuit

TYPICAL CHARACTERISTICS

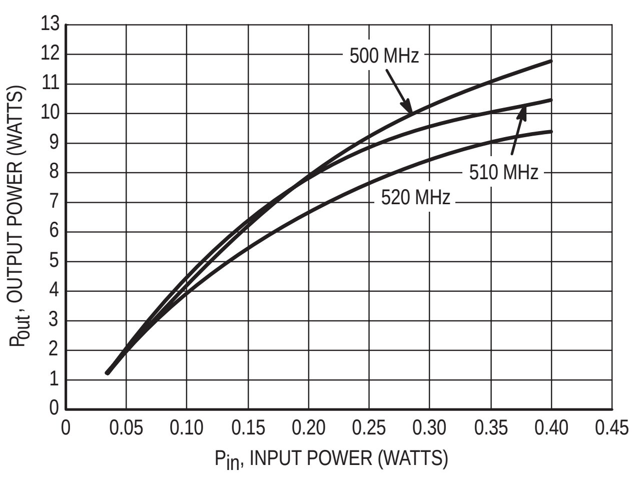


Figure 2. Output Power versus Input Power

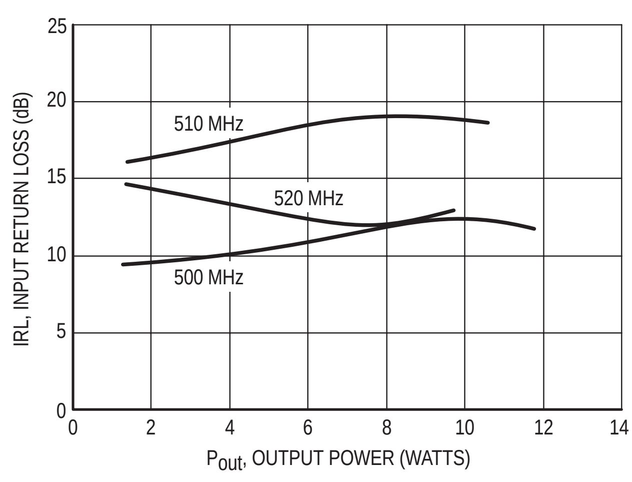


Figure 3. Input Return Loss versus Output Power

TYPICAL CHARACTERISTICS

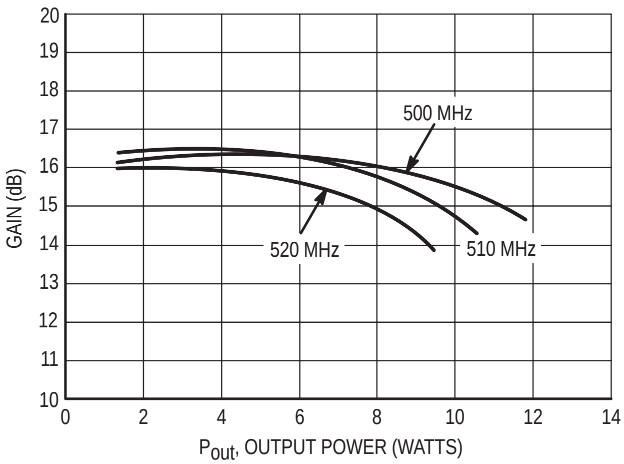


Figure 4. Gain versus Output Power

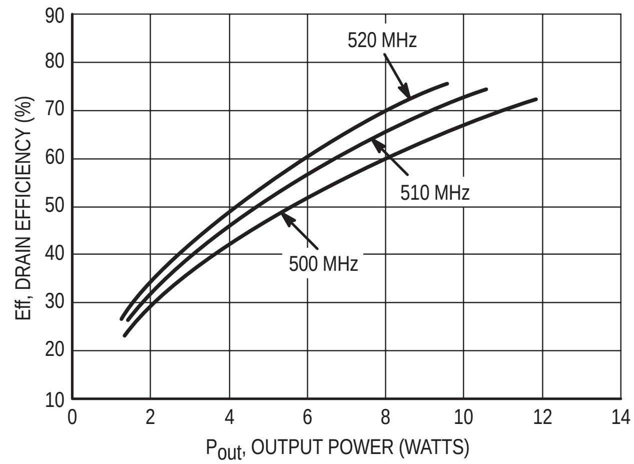


Figure 5. Drain Efficiency versus Output Power

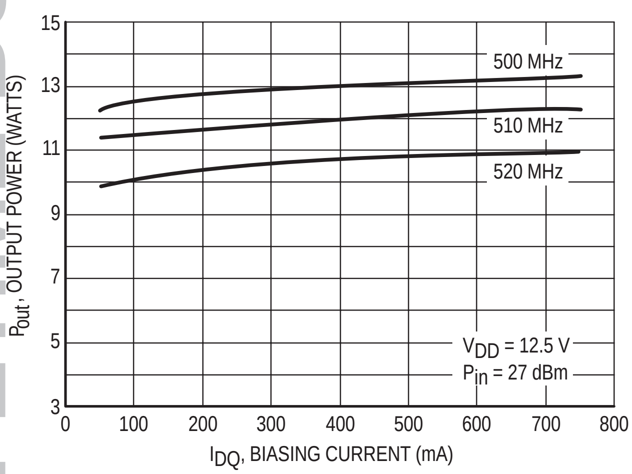


Figure 6. Output Power versus Biasing Current

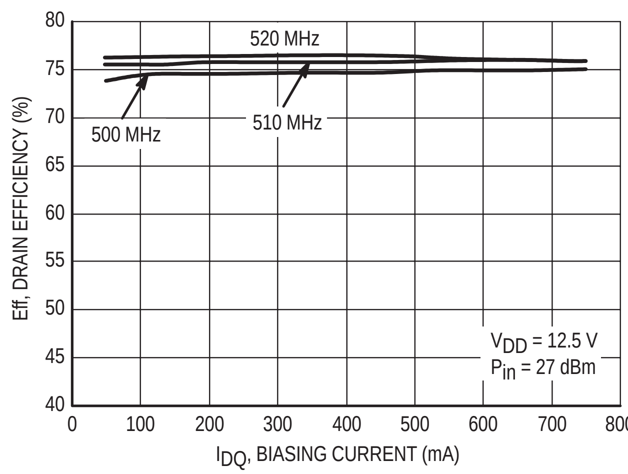


Figure 7. Drain Efficiency versus Biasing Current

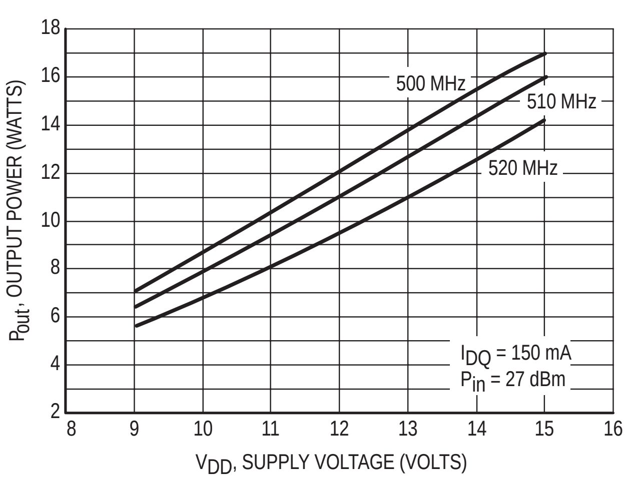


Figure 8. Output Power versus Supply Voltage

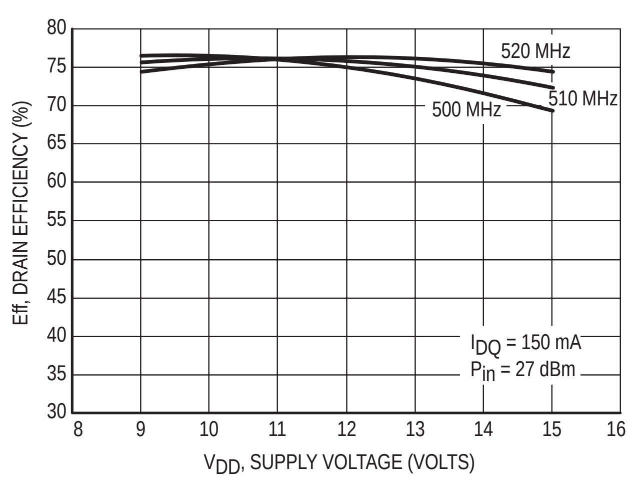
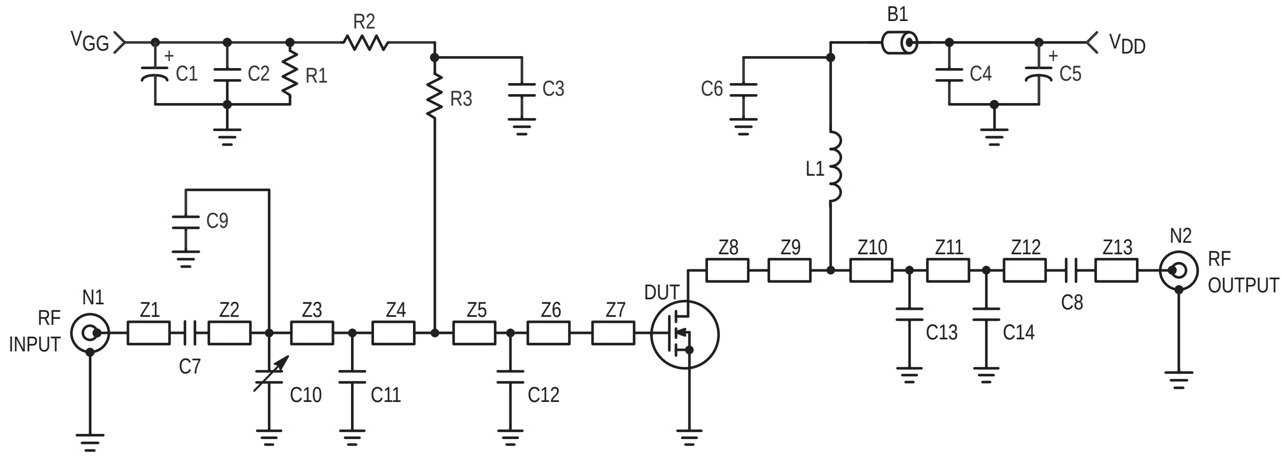


Figure 9. Drain Efficiency versus Supply Voltage



B1	Fair Rite Products Long Ferrite Bead
C1, C5	10 µF, 50 V Electrolytic Capacitor
C2, C4	0.1 µF, 100 mil Chip Capacitor
C3, C6, C7, C8	130 pF, 100 mil Chip Capacitor
C9	10 pF, 100 mil Chip Capacitor
C10	0.8–8 pF, Variable Capacitor, Gigatrim
C11	47 pF, 100 mil Chip Capacitor
C12	16 pF, 100 mil Chip Capacitor
C13	6.2 pF, 100 mil Chip Capacitor
C14	5.1 pF, 100 mil Chip Capacitor
L1	4 Turns, #20 AWG Enamel Coil, 0.1″ ID
N1, N2	Type–N Flange Mount Connector
R1	1.1 MΩ, 1/4 W Carbon Resistor
R2	1.0 kΩ, 0.1 W Chip Resistor
R3	1 kΩ, 1/4 W Carbon Resistor
Z1, Z13	0.290″ x 0.081″ Microstrip
Z2	0.150″ x 0.217″ Microstrip
Z3	2.650″ x 0.217″ Microstrip
Z4	0.200″ x 0.217″ Microstrip
Z5	0.300″ x 0.217″ Microstrip
Z6	0.050″ x 0.217″ Microstrip
Z7, Z8	0.313″ x 0.160″ Microstrip
Z9	0.200″ x 0.217″ Microstrip
Z10	0.800″ x 0.217″ Microstrip
Z11	2.400″ x 0.217″ Microstrip
Z12	0.100″ x 0.217″ Microstrip
Board	Glass Teflon®, 31 mils, 2 oz. Copper
Insert	Glass Teflon®, 31 mils, 2 oz. Copper

Figure 10. 400 – 470 MHz Broadband Test Circuit

TYPICAL CHARACTERISTICS

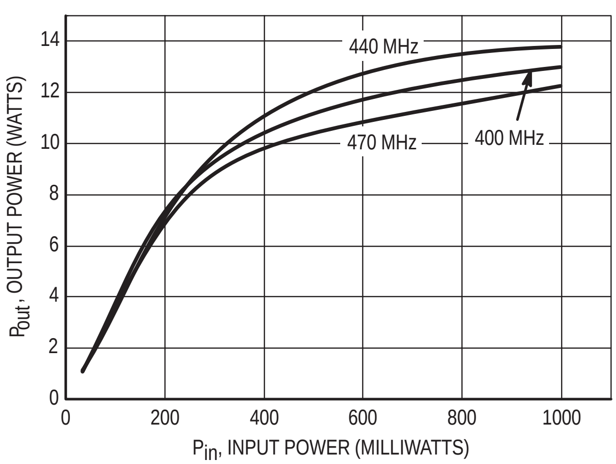


Figure 11. Output Power versus Input Power

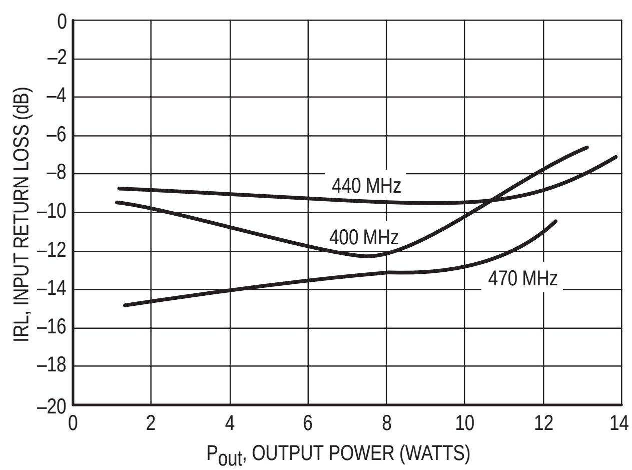


Figure 12. Input Return Loss versus Output Power

TYPICAL CHARACTERISTICS

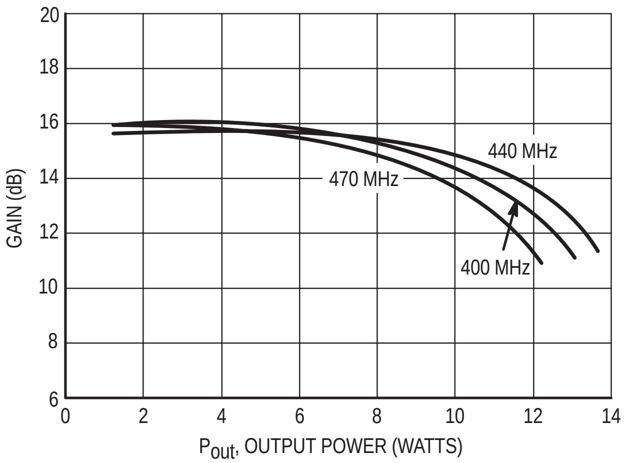


Figure 13. Gain versus Output Power

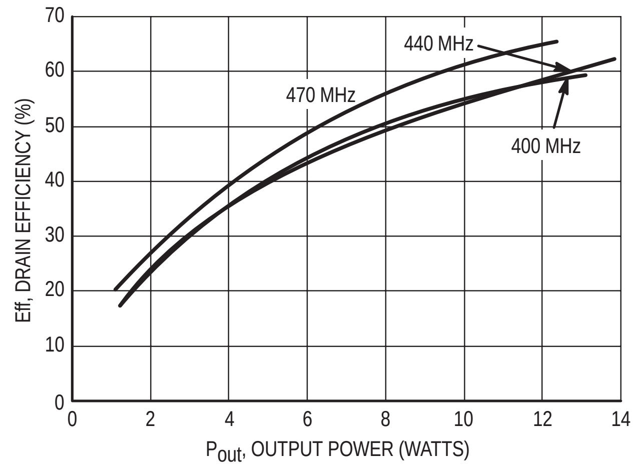


Figure 14. Drain Efficiency versus Output Power

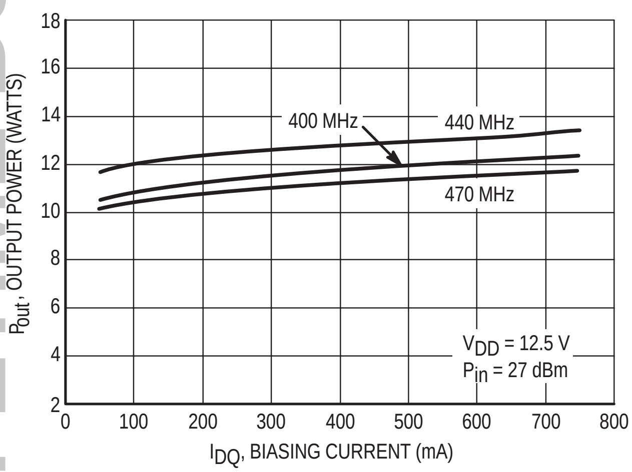


Figure 15. Output Power versus Biasing Current

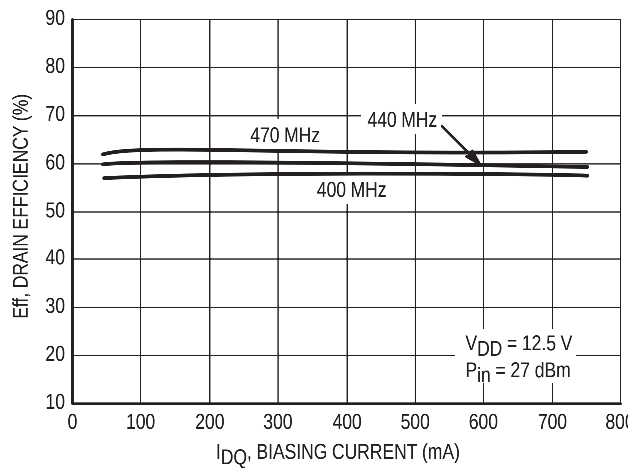


Figure 16. Drain Efficiency versus Biasing Current

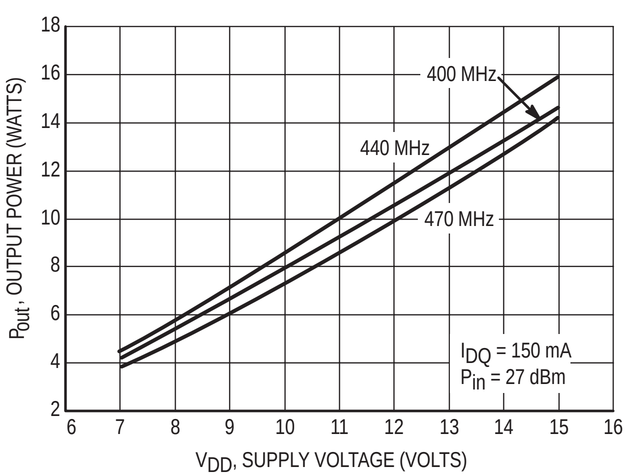


Figure 17. Output Power versus Supply Voltage

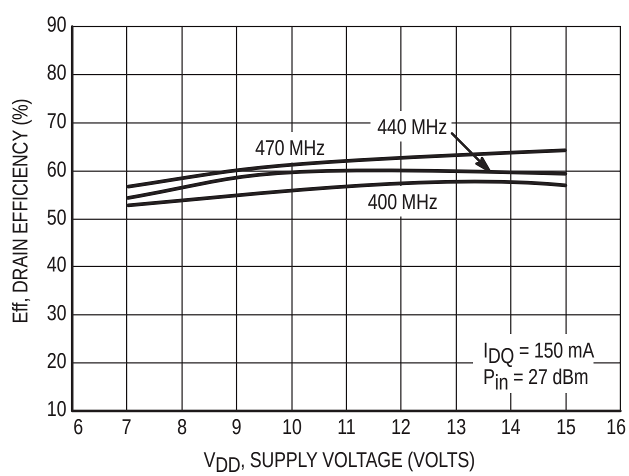
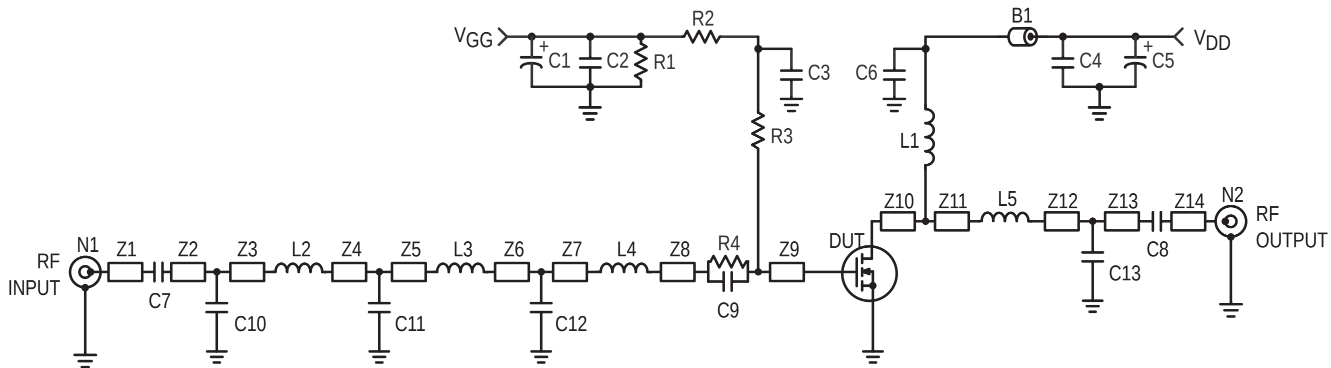


Figure 18. Drain Efficiency versus Supply Voltage



B1	Fair Rite Products Long Ferrite Bead
C1, C5	10 µF, 50 V Electrolytic Capacitor
C2, C4	0.1 µF, 100 mil Chip Capacitor
C3, C6, C7, C8	130 pF, 100 mil Chip Capacitor
C9	82 pF, 100 mil Chip Capacitor
C10	6.2 pF, 100 mil Chip Capacitor
C11	30 pF, 100 mil Chip Capacitor
C12	75 pF, 100 mil Chip Capacitor
C13	39 pF, 100 mil Chip Capacitor
L1	4 Turns, #20 AWG Enamel Coil, 0.1″ ID
L2	17.5 nH Air Core Inductor, Coilcraft A06T
L3	22 nH Air Core Inductor, Coilcraft A07T
L4	18.5 nH Air Core Inductor, Coilcraft A05T
L5	5 nH Air Core Inductor, Coilcraft A02T
N1, N2	Type–N Flange Mount Connector
R1	1.1 MΩ, 1/4 W Carbon Resistor
R2	1.0 kΩ, 0.1 W Chip Resistor
R3	50 Ω, 1/4 W Carbon Resistor
R4	20 Ω, 0.1 W Chip Resistor
Z1	0.200″ x 0.081″ Microstrip
Z2	0.050″ x 0.081″ Microstrip
Z3	0.450″ x 0.081″ Microstrip
Z4	0.050″ x 0.081″ Microstrip
Z5	0.550″ x 0.081″ Microstrip
Z6	0.350″ x 0.081″ Microstrip
Z7	1.150″ x 0.081″ Microstrip
Z8	0.250″ x 0.081″ Microstrip
Z9	0.350″ x 0.081″ Microstrip
Z10	0.500″ x 0.081″ Microstrip
Z11	1.150″ x 0.081″ Microstrip
Z12	1.450″ x 0.081″ Microstrip
Z13	0.050″ x 0.081″ Microstrip
Z14	0.200″ x 0.081″ Microstrip
Board	Glass Teflon®, 31 mils, 2 oz. Copper

Figure 19. 136 – 175 MHz Broadband Test Circuit

TYPICAL CHARACTERISTICS

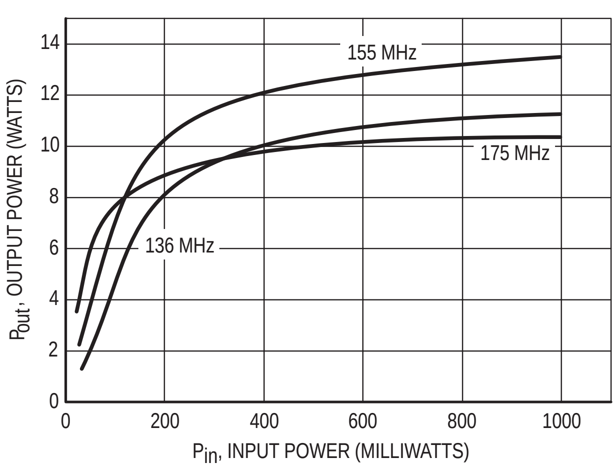


Figure 20. Output Power versus Input Power

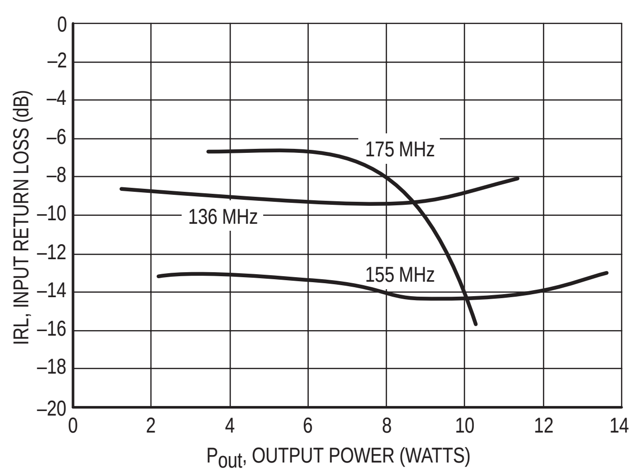


Figure 21. Input Return Loss versus Output Power

TYPICAL CHARACTERISTICS

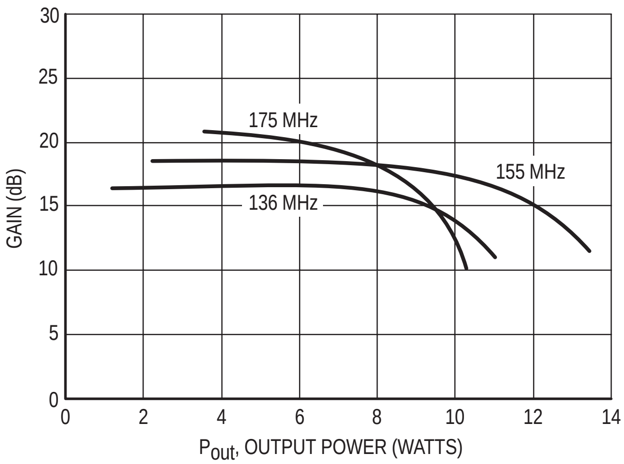


Figure 22. Gain versus Output Power

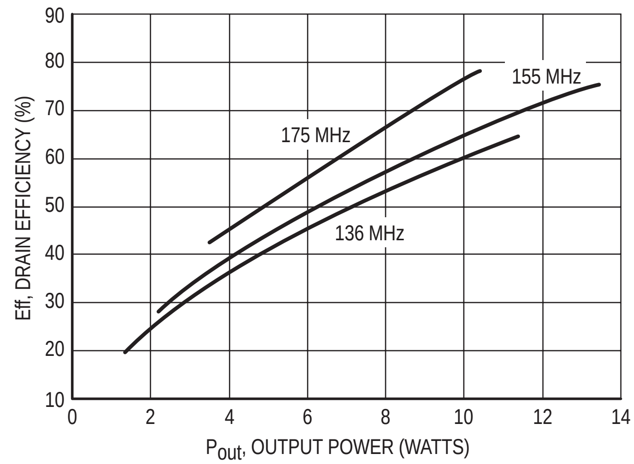


Figure 23. Drain Efficiency versus Output Power

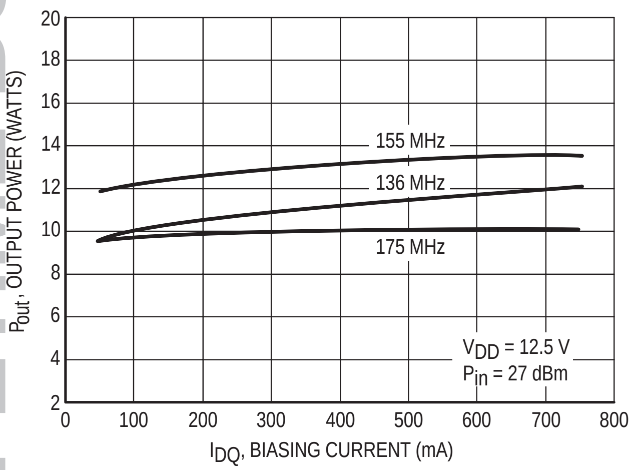


Figure 24. Output Power versus Biasing Current

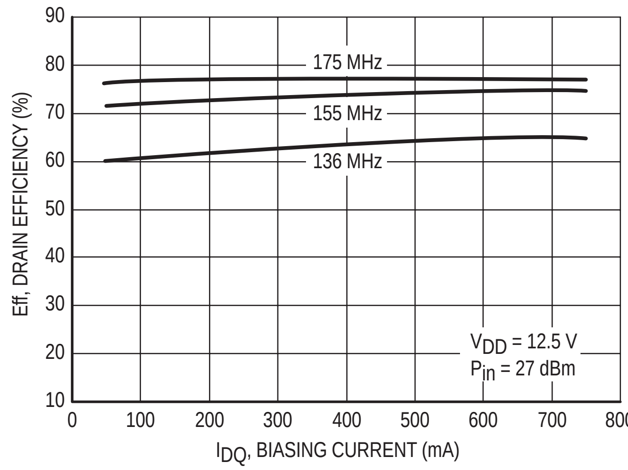


Figure 25. Drain Efficiency versus Biasing Current

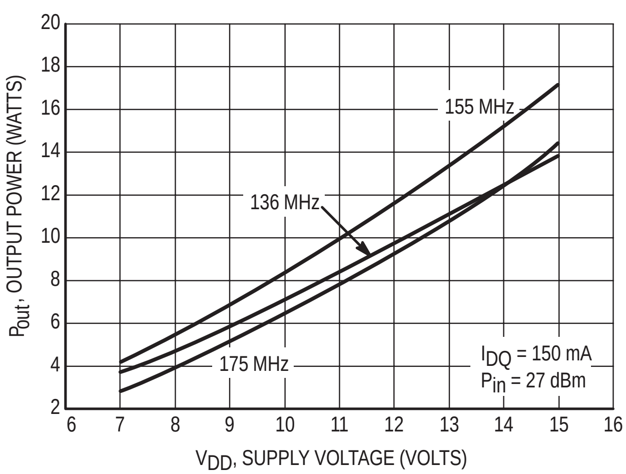


Figure 26. Output Power versus Supply Voltage

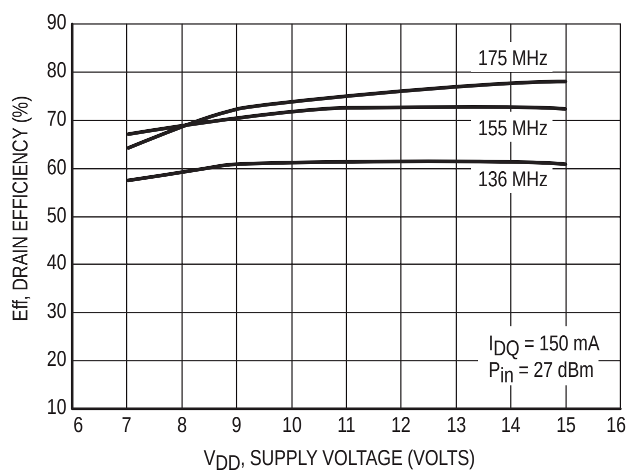
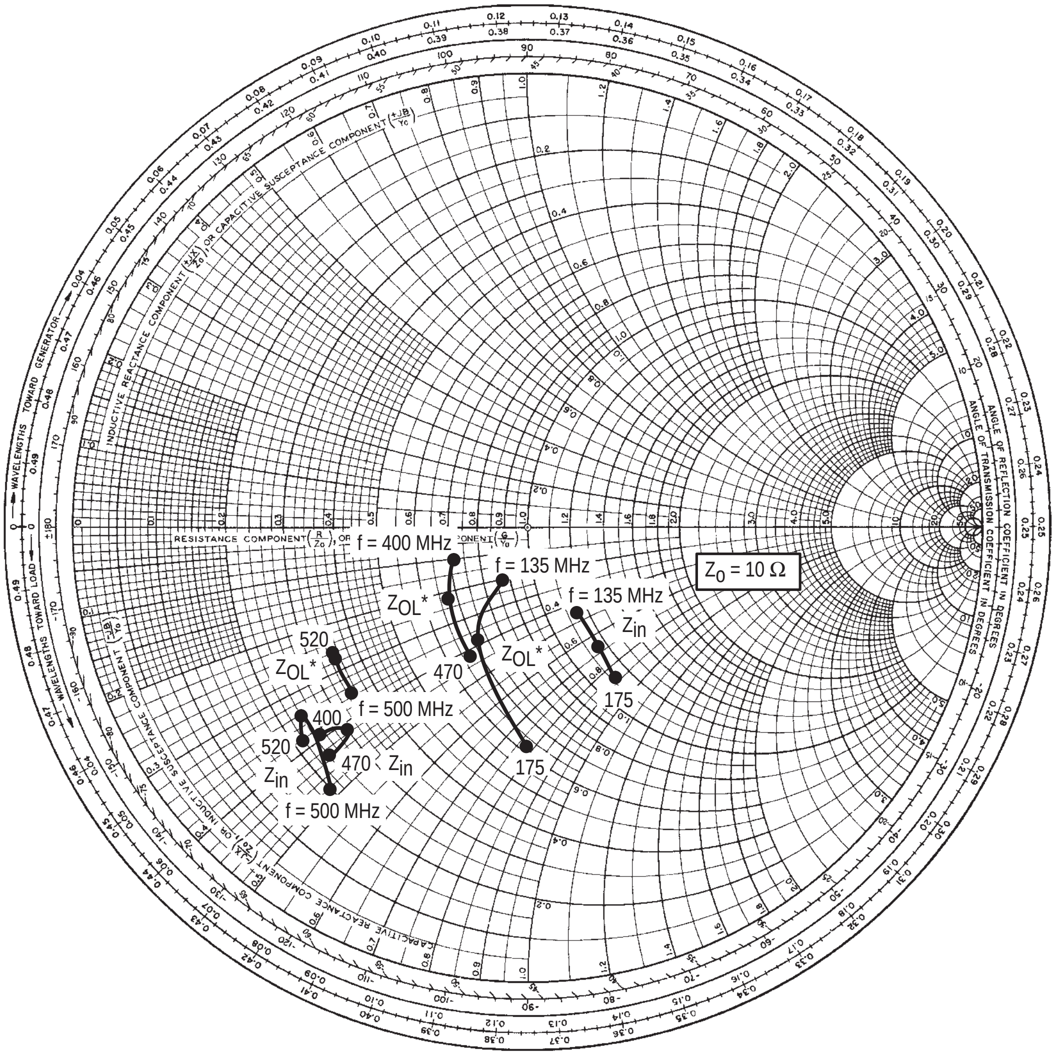


Figure 27. Drain Efficiency versus Supply Voltage



V_{DD} = 12.5 V, I_{DQ} = 150 mA, P_{out} = 8 W

f MHz	Z_{in} Ω	Z_{OL}* Ω
500	2.0 – j4.8	3.5 – j3.5
510	2.4 – j3.4	3.5 – j2.7
520	2.2 – j3.8	3.5 – j2.6

Z_{in} = Conjugate of source impedance with parallel 20 Ω resistor and 82 pF capacitor in series with gate. (See Figure 1).

Z_{OL}* = Conjugate of the load impedance at given output power, voltage, frequency, and η_D > 50 %.

V_{DD} = 12.5 V, I_{DQ} = 150 mA, P_{out} = 8 W

f MHz	Z_{in} Ω	Z_{OL}* Ω
400	2.5 – j3.9	7.1 – j0.1
440	3.0 – j4.1	6.8 – j2.3
470	2.4 – j4.3	6.8 – j4.2

Z_{in} = Conjugate of source impedance with parallel 20 Ω resistor and 82 pF capacitor in series with gate. (See Figure 10).

Z_{OL}* = Conjugate of the load impedance at given output power, voltage, frequency, and η_D > 50 %.

V_{DD} = 12.5 V, I_{DQ} = 150 mA, P_{out} = 8 W

f MHz	Z_{in} Ω	Z_{OL}* Ω
135	11.7 – j4.4	8.7 – j0.2
155	11.8 – j6.8	7.2 – j3.8
175	11.3 – j8.8	6.3 – j7.7

Z_{in} = Conjugate of source impedance with parallel 20 Ω resistor and 82 pF capacitor in series with gate. (See Figure 19).

Z_{OL}* = Conjugate of the load impedance at given output power, voltage, frequency, and η_D > 50 %.

Note: Z_{OL}* was chosen based on tradeoffs between gain, drain efficiency, and device stability.

Figure 28. Series Equivalent Input and Output Impedance

Table 1. Common Source Scattering Parameters (V_{DS} = 12.5 Vdc, I_{DQ} = 150 mA)

f MHz	S_{11}		S_{21}		S_{12}		S_{22}	
	$\|S_{11}\|$	φ	$\|S_{21}\|$	φ	$\|S_{12}\|$	φ	$\|S_{22}\|$	φ
50	0.770	–136	16.04	101	0.040	12	0.670	–137
100	0.760	–154	8.15	86	0.040	–3	0.680	–153
150	0.770	–160	5.30	77	0.040	–11	0.700	–158
200	0.780	–163	3.83	70	0.040	–18	0.720	–160
250	0.800	–165	2.91	64	0.040	–23	0.750	–161
300	0.820	–166	2.29	58	0.030	–27	0.780	–162
350	0.840	–167	1.87	54	0.030	–31	0.800	–163
400	0.850	–168	1.54	50	0.030	–35	0.820	–164
450	0.860	–168	1.29	47	0.030	–38	0.840	–165
500	0.870	–169	1.09	44	0.030	–39	0.850	–166
550	0.880	–170	0.96	41	0.020	–42	0.870	–166
600	0.890	–170	0.83	39	0.020	–43	0.880	–167
650	0.900	–171	0.72	37	0.020	–44	0.890	–168
700	0.910	–171	0.65	35	0.020	–44	0.890	–168
750	0.910	–172	0.59	32	0.020	–45	0.900	–169
800	0.920	–172	0.52	30	0.020	–48	0.910	–169
850	0.930	–173	0.46	29	0.020	–50	0.910	–170
900	0.930	–173	0.42	28	0.010	–51	0.920	–170
950	0.930	–173	0.38	26	0.010	–54	0.920	–170
1000	0.930	–173	0.35	24	0.010	–52	0.920	–171
1050	0.930	–174	0.31	23	0.010	–51	0.930	–171
1100	0.930	–174	0.28	22	0.010	–45	0.930	–171
1150	0.940	–174	0.26	21	0.010	–53	0.930	–172
1200	0.940	–174	0.24	21	0.010	–60	0.930	–172

Table 2. Common Source Scattering Parameters (V_{DS} = 12.5 Vdc, I_{DQ} = 800 mA)

f MHz	S_{11}		S_{21}		S_{12}		S_{22}	
	$\|S_{11}\|$	ϕ	$\|S_{21}\|$	ϕ	$\|S_{12}\|$	ϕ	$\|S_{22}\|$	ϕ
50	0.840	–152	19.13	99	0.020	10	0.740	–158
100	0.820	–165	9.60	88	0.020	0	0.760	–167
150	0.820	–169	6.33	82	0.020	–6	0.760	–170
200	0.830	–171	4.68	77	0.020	–10	0.770	–170
250	0.830	–172	3.64	73	0.020	–13	0.780	–171
300	0.840	–172	2.94	69	0.020	–15	0.790	–171
350	0.850	–173	2.48	66	0.020	–18	0.800	–171
400	0.850	–173	2.09	62	0.020	–21	0.810	–171
450	0.860	–173	1.80	60	0.020	–22	0.820	–170
500	0.870	–174	1.56	57	0.020	–24	0.830	–171
550	0.870	–174	1.39	54	0.020	–25	0.840	–171
600	0.880	–174	1.23	52	0.020	–27	0.850	–171
650	0.880	–174	1.09	50	0.020	–26	0.860	–171
700	0.890	–174	1.00	48	0.010	–28	0.860	–171
750	0.900	–174	0.91	45	0.010	–29	0.870	–172
800	0.900	–174	0.82	43	0.010	–31	0.870	–172
850	0.910	–175	0.74	41	0.010	–32	0.880	–172
900	0.910	–175	0.68	40	0.010	–32	0.880	–172
950	0.910	–175	0.62	37	0.010	–36	0.880	–172
1000	0.910	–175	0.56	36	0.010	–33	0.880	–173
1050	0.920	–175	0.51	34	0.010	–35	0.880	–172
1100	0.920	–175	0.46	33	0.010	–25	0.890	–173
1150	0.920	–175	0.43	33	0.010	–34	0.880	–173
1200	0.920	–175	0.39	32	0.010	–40	0.880	–173

Table 3. Common Source Scattering Parameters (V_{DS} = 12.5 Vdc, I_{DQ} = 1.5 A)

f MHz	S_{11}		S_{21}		S_{12}		S_{22}	
	$\|S_{11}\|$	φ	$\|S_{21}\|$	φ	$\|S_{12}\|$	φ	$\|S_{22}\|$	φ
50	0.860	–152	18.90	100	0.020	11	0.740	–160
100	0.830	–165	9.46	89	0.020	1	0.770	–168
150	0.830	–169	6.24	83	0.020	–4	0.770	–171
200	0.840	–171	4.61	78	0.020	–9	0.780	–171
250	0.840	–172	3.59	74	0.020	–12	0.790	–171
300	0.840	–173	2.91	70	0.020	–15	0.800	–171
350	0.850	–173	2.45	67	0.020	–17	0.810	–171
400	0.860	–174	2.07	63	0.020	–20	0.820	–171
450	0.860	–174	1.78	60	0.020	–21	0.820	–171
500	0.870	–174	1.55	58	0.020	–22	0.840	–171
550	0.880	–174	1.39	55	0.020	–24	0.840	–171
600	0.880	–174	1.23	53	0.020	–24	0.850	–171
650	0.890	–175	1.09	51	0.010	–24	0.860	–172
700	0.890	–175	1.00	49	0.010	–25	0.860	–172
750	0.900	–175	0.91	46	0.010	–27	0.870	–172
800	0.900	–175	0.82	43	0.010	–28	0.870	–172
850	0.910	–175	0.74	42	0.010	–31	0.870	–173
900	0.910	–175	0.68	40	0.010	–30	0.870	–173
950	0.910	–175	0.62	38	0.010	–32	0.870	–173
1000	0.910	–175	0.56	36	0.010	–31	0.860	–173
1050	0.920	–175	0.51	35	0.010	–29	0.860	–173
1100	0.920	–175	0.46	34	0.010	–22	0.860	–173
1150	0.920	–175	0.43	34	0.010	–30	0.850	–173
1200	0.920	–175	0.39	33	0.010	–35	0.850	–172

APPLICATIONS INFORMATION

DESIGN CONSIDERATIONS

The MRF1508 is a common–source, RF power, N–Channel enhancement mode, Lateral Metal–Oxide Semiconductor Field–Effect Transistor (MOSFET). Motorola Application Note AN211A, “FETs in Theory and Practice”, is suggested reading for those not familiar with the construction and characteristics of FETs.

This surface mount packaged device was designed primarily for VHF and UHF portable power amplifier applications. Manufacturability is improved by utilizing the tape and reel capability for fully automated pick and placement of parts. However, care should be taken in the design process to insure proper heat sinking of the device.

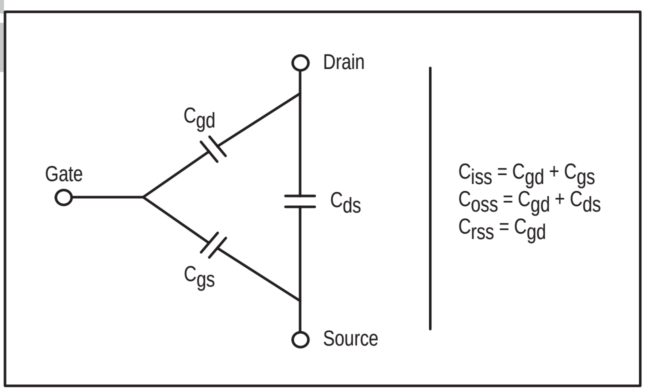
The major advantages of Lateral RF power MOSFETs include high gain, simple bias systems, relative immunity from thermal runaway, and the ability to withstand severely mismatched loads without suffering damage.

MOSFET CAPACITANCES

The physical structure of a MOSFET results in capacitors between all three terminals. The metal oxide gate structure determines the capacitors from gate–to–drain (C_{gd}), and gate–to–source (C_{gs}). The PN junction formed during fabrication of the RF MOSFET results in a junction capacitance from drain–to–source (C_{ds}). These capacitances are characterized as input (C_{iss}), output (C_{oss}) and reverse transfer (C_{rss}) capacitances on data sheets. The relationships between the inter–terminal capacitances and those given on data sheets are shown below. The C_{iss} can be specified in two ways:

1. Drain shorted to source and positive voltage at the gate.
2. Positive voltage of the drain in respect to source and zero volts at the gate.

In the latter case, the numbers are lower. However, neither method represents the actual operating conditions in RF applications.



DRAIN CHARACTERISTICS

One critical figure of merit for a FET is its static resistance in the full–on condition. This on–resistance, $R_{DS(on)}$, occurs in the linear region of the output characteristic and is specified at a specific gate–source voltage and drain current. The drain–source voltage under these conditions is termed $V_{DS(on)}$. For MOSFETs, $V_{DS(on)}$ has a positive temperature coefficient at high temperatures because it contributes to the power dissipation within the device.

BV_{DSS} values for this device are higher than normally required for typical applications. Measurement of BV_{DSS} is not recommended and may result in possible damage to the device.

GATE CHARACTERISTICS

The gate of the RF MOSFET is a polysilicon material, and is electrically isolated from the source by a layer of oxide. The DC input resistance is very high – on the order of 10^9 Ω — resulting in a leakage current of a few nanoamperes.

Gate control is achieved by applying a positive voltage to the gate greater than the gate–to–source threshold voltage, $V_{GS(th)}$.

Gate Voltage Rating — Never exceed the gate voltage rating. Exceeding the rated V_{GS} can result in permanent damage to the oxide layer in the gate region.

Gate Termination — The gates of these devices are essentially capacitors. Circuits that leave the gate open–circuited or floating should be avoided. These conditions can result in turn–on of the devices due to voltage build–up on the input capacitor due to leakage currents or pickup.

Gate Protection — These devices do not have an internal monolithic zener diode from gate–to–source. If gate protection is required, an external zener diode is recommended. Using a resistor to keep the gate–to–source impedance low also helps dampen transients and serves another important function. Voltage transients on the drain can be coupled to the gate through the parasitic gate–drain capacitance. If the gate–to–source impedance and the rate of voltage change on the drain are both high, then the signal coupled to the gate may be large enough to exceed the gate–threshold voltage and turn the device on.

DC BIAS

Since the MRF1508 is an enhancement mode FET, drain current flows only when the gate is at a higher potential than the source. RF power FETs operate optimally with a quiescent drain current (I_{DQ}), whose value is application dependent. The MRF1508 was characterized at I_{DQ} = 150 mA, which is the suggested value of bias current for typical applications. For special applications such as linear amplification, I_{DQ} may have to be selected to optimize the critical parameters.

The gate is a dc open circuit and draws no current. Therefore, the gate bias circuit may generally be just a simple resistive divider network. Some special applications may require a more elaborate bias system.

GAIN CONTROL

Power output of the MRF1508 may be controlled to some degree with a low power dc control signal applied to the gate, thus facilitating applications such as manual gain control, ALC/AGC and modulation systems. This characteristic is very dependent on frequency and load line.

MOUNTING

The specified maximum thermal resistance of 2°C/W assumes a majority of the 0.065″ x 0.180″ source contact on the back side of the package is in good contact with an appropriate heat sink. As with all RF power devices, the goal of the thermal design should be to minimize the temperature at the back side of the package. Refer to Motorola Application Note AN4005/D, “Thermal Management and Mounting Method for the PLD–1.5 RF Power Surface Mount Package,” and Engineering Bulletin EB209/D, “Mounting Method for RF Power Leadless Surface Mount Transistor” for additional information.

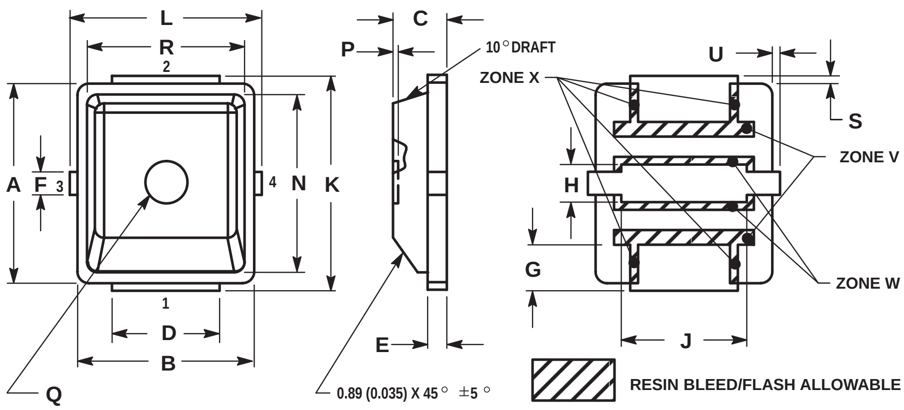
AMPLIFIER DESIGN

Impedance matching networks similar to those used with bipolar transistors are suitable for the MRF1508. For examples see Motorola Application Note AN721, “Impedance Matching Networks Applied to RF Power Transistors.” Large–signal impedances are provided, and will yield a good first pass approximation.

Since RF power MOSFETs are triode devices, they are not unilateral. This coupled with the very high gain of the MRF1508 yields a device capable of self oscillation. Stability may be achieved by techniques such as drain loading, input shunt resistive loading, or output to input feedback. The RF test fixture implements a parallel resistor and capacitor in series with the gate, and has a load line selected for a higher efficiency, lower gain, and more stable operating region.

Two–port stability analysis with the MRF1508 S–parameters provides a useful tool for selection of loading or feedback circuitry to assure stable operation. See Motorola Application Note AN215A, “RF Small–Signal Design Using Two–Port Parameters” for a discussion of two port network theory and stability.

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH
3. RESIN BLEED/FLASH ALLOWABLE IN ZONE V, W, AND X.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.255	0.265	6.48	6.73
B	0.225	0.235	5.72	5.97
C	0.065	0.072	1.65	1.83
D	0.130	0.150	3.30	3.81
E	0.021	0.026	0.53	0.66
F	0.026	0.044	0.66	1.12
G	0.050	0.070	1.27	1.78
H	0.045	0.063	1.14	1.60
J	0.160	0.180	4.06	4.57
K	0.273	0.285	6.93	7.24
L	0.245	0.255	6.22	6.48
N	0.230	0.240	5.84	6.10
P	0.000	0.008	0.00	0.20
Q	0.055	0.063	1.40	1.60
R	0.200	0.210	5.08	5.33
S	0.006	0.012	0.15	0.31
U	0.006	0.012	0.15	0.31
ZONE V	0.000	0.021	0.00	0.53
ZONE W	0.000	0.010	0.00	0.25
ZONE X	0.000	0.010	0.00	0.25

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE
4. SOURCE

CASE 466–02
ISSUE B

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